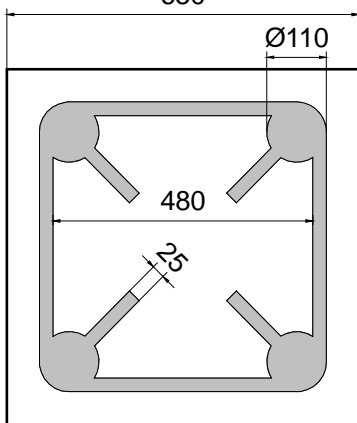


Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	P (anode) up

 <p style="text-align: center;">LED-07</p>	typ. dimensions (µm)	
	typ. thickness 150 (±25) µm  <u>cathode</u> gold alloy, 0.5 µm  <u>anode</u> gold alloy, 1.5 µm	

**Optical and Electrical Characteristics**

T<sub>amb</sub> = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I <sub>F</sub> = 20 mA	V <sub>F</sub>		1.20		V
Forward voltage <sup>2</sup>	I <sub>F</sub> = 350 mA	V <sub>F</sub>		1.45		V
Reverse voltage	I <sub>R</sub> = 10 µA	V <sub>R</sub>	5			V
Radiant power <sup>1</sup>	I <sub>F</sub> = 20 mA	Φ <sub>e</sub>		2.5		mW
Radiant power <sup>2</sup>	I <sub>F</sub> = 350 mA	Φ <sub>e</sub>		20		mW
Radiant intensity <sup>1</sup>	I <sub>F</sub> = 20 mA	I <sub>e</sub>		0.75		mW/sr
Radiant intensity <sup>2</sup>	I <sub>F</sub> = 350 mA	I <sub>e</sub>		12		mW/sr
Peak wavelength	I <sub>F</sub> = 20 mA	λ <sub>P</sub>	900	910	920	nm
Spectral bandwidth at 50%	I <sub>F</sub> = 20 mA	Δλ <sub>0.5</sub>		60		nm
Switching time	I <sub>F</sub> = 20 mA	t <sub>r</sub> , t <sub>f</sub>		40		ns

<sup>1</sup>Measured on bare chip on TO-18 header

<sup>2</sup>Measured on bare chip glued on a Ø 8 x 1mm Cu header (10 s after switched on) (for information only)

**Labeling**

Type	Lot N°	Φ <sub>e</sub> (typ) [mW]	V <sub>F</sub> (typ) [V]	Quantity
ELC-910-12				

**Packing:** Chips on adhesive film with wire-bond side on top

\*Note: All measurements carried out on *EPIGAP* equipment